

	L #	Hits	Search Text	DBs	Time Stamp
1	L2	886407	inverse\$2 (2n) thickness\$2	EPO; JPO; DERWENT	2006/09/25 15:50
2	L6	105061	2 with layer	EPO; JPO	2006/09/25 15:35
3	L7	10914	6 same semiconductor	EPO; JPO	2006/09/25 15:34
4	L8	1464	6 same spacer	EPO; JPO	2006/09/25 15:35
5	L9	9	6 same flash adj memory	EPO; JPO	2006/09/25 15:34
6	L10	3186	2 with insulating adj layer	EPO; JPO	2006/09/25 15:35
7	L11	55	10 same spacer	EPO; JPO	2006/09/25 15:42
8	L12	1123	10 same substrate	EPO; JPO	2006/09/25 15:42
9	L13	1103	12 not 11	EPO; JPO	2006/09/25 15:43
10	L21	229	inverse\$2 near2 thickness\$2	EPO; JPO; DERWENT	2006/09/25 15:50
11	L22	236	inverse\$2 near2 (thickness\$2 thick)	EPO; JPO; DERWENT	2006/09/25 15:59
12	L23	48	22 and (substrate or semiconductor)	EPO; JPO; DERWENT	2006/09/25 16:05
13	L25	13	("4711514").URPN.	USPAT	2006/09/25 15:55
14	L26	387	inverse\$2 near4 (thickness\$2 thick)	EPO; JPO; DERWENT	2006/09/25 16:04
15	L27	339	26 not 23	EPO; JPO; DERWENT	2006/09/25 16:00
16	L28	35	27 and (substrate or semiconductor)	EPO; JPO; DERWENT	2006/09/25 16:17
17	L29	2523	opposite\$2 near4 (thickness\$2 thick)	EPO; JPO; DERWENT	2006/09/25 16:05
18	L30	1018	opposite\$2 near2 (thickness\$2 thick)	EPO; JPO; DERWENT	2006/09/25 16:05

	L #	Hits	Search Text	DBs	Time Stamp
19	L32	175	30 and (substrate or semiconductor)	EPO; JPO; DERWENT	2006/09/25 16:16
20	L35	16700	gradual\$2 near3 (thinner thicker thickness thinness)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	2006/09/25 16:43
21	L36	641	35 and (substrate or semiconductor)	EPO; JPO; DERWENT	2006/09/25 16:45
22	L37	308	35 and semiconductor	EPO; JPO; DERWENT	2006/09/25 16:17
23	L44	7623	increased near3 (thinner thicker thickness thinness)	EPO; JPO; DERWENT	2006/09/25 16:45
24	L45	7807	decreas\$5 near3 (thinner thicker thickness thinness)	EPO; JPO; DERWENT	2006/09/25 16:44
25	L46	2001	decreased near3 (thinner thicker thickness thinness)	EPO; JPO; DERWENT	2006/09/25 16:45
26	L47	15028	44 45 46	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	2006/09/25 16:45
27	L48	3048	47 and (substrate or semiconductor)	EPO; JPO; DERWENT	2006/09/25 16:45
28	L49	1479	47 and semiconductor	EPO; JPO; DERWENT	2006/09/25 16:45
29	L50	1476	49 not 32	EPO; JPO; DERWENT	2006/09/25 16:46
30	L51	917	50 and layer	EPO; JPO; DERWENT	2006/09/25 17:01